SN74LVC3G17 Triple Schmitt-Trigger Buffer

1 Features

- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Maximum t_{pd} of 5.4 ns at 3.3 V
- Low Power Consumption, 10-µA Maximum I_{CC}
- ±24-mA Output Drive at 3.3 V
- Typical V_{OLP} (Output Ground Bounce) <0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot) >2 V at V_{CC} = 3.3 V, T_A = 25°C
- I_{off} Supports Live Insertion, Partial-Power-Down Mode and Back Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human Body Model (A114-A)
  - 200-V Machine Model (A115-A)
  - 1000-V Charged-Device Model (C101)

2 Applications

- AV Receivers
- Audio Docks: Portable
- Blu-ray® Players and Home Theater
- MP3 Players/Recorders
- Personal Digital Assistants (PDAs)
- Power: Telecom/Server AC/DC Supply: Single Controller: Analog and Digital
- Solid State Drives (SSDs): Client and Enterprise
- TVs: LCD/Digital and High-Definition (HDTVs)
- Tablets: Enterprise
- Video Analytics: Server
- Wireless Headsets, Keyboards, and Mice

3 Description

This triple Schmitt-trigger buffer is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC3G17 device contains three buffers and performs the Boolean function Y = A. The device functions as three independent buffers but, because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

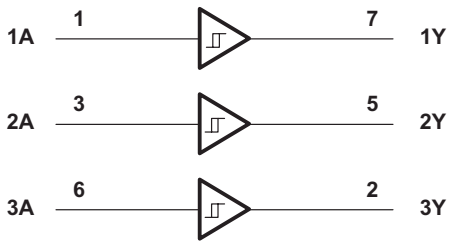
NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74LVC3G17DCT	SSOP (8)	2.95 mm × 2.80 mm
SN74LVC3G17DCU	VSSOP (8)	2.30 mm × 2.00 mm
SN74LVC3G17YZP	DSBGA (8)	1.91 mm × 0.91 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (November 2013) to Revision F — **Page**

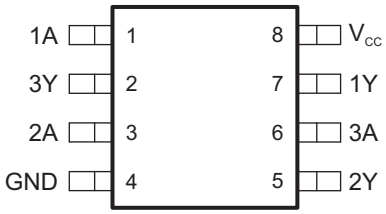
- Added the *Device Information* table, *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 1
- Moved T_{stg} to *Absolute Maximum Ratings* table ... 4

Changes from Revision D (Feburary 2007) to Revision E — **Page**

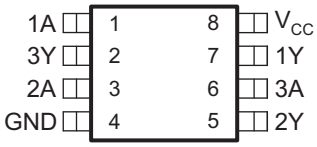
- Updated document to new TI data sheet format. ... 1
- Updated operating temperature range. ... 4

5 Pin Configuration and Functions

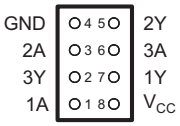
DCT Package
8-Pin SSOP
Top View



DCU Package
8-Pin VSSOP
Top View



YZP Package
8-Pin DSBGA
Bottom View



See mechanical drawing for dimensions.

Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
1A	1	I	Input 1
1Y	7	O	Output 1
2A	3	I	Input 2
2Y	5	O	Output 2
3A	6	I	Input 3
3Y	2	O	Output 3
GND	4	—	Ground
V_{CC}	8	—	Power Pin

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	6.5	V
V_I	Input voltage(2)		–0.5	6.5	V
V_O	Voltage applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Output voltage(2)(3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

			VALUE	UNIT
V_{ESD}	Electrostatic discharge	Human Body Model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	+2000	V
		Charged-Device Model (CDM), per JEDEC specification JESD22-C101, all pins(2)	+1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

See (1).

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
T_A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

6.4 Thermal Information

THERMAL METRIC[1]		SNLVC3G17			UNIT
		DCT (SSOP)	DCU (VSSOP)	YZP (DSBGA)	
		6 PINS	6 PINS	6 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance[2]	220	227	102	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.
(2) The package thermal impedance is calculated in accordance with JESD 51-7.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	–40°C to 85°C			–40°C to 125°C			UNIT
			MIN	TYP[1]	MAX	MIN	TYP[1]	MAX	
V_{T+} Positive-going input threshold voltage		1.65 V	0.79		1.16	0.79		1.16	V
		2.3 V	1.11		1.56	1.11		1.56	
		3 V	1.5		1.87	1.5		1.87	
		4.5 V	2.16		2.74	2.16		2.74	
		5.5 V	2.61		3.33	2.61		3.33	
V_{T-} Negative-going input threshold voltage		1.65 V	0.39		0.62	0.39		0.62	V
		2.3 V	0.58		0.87	0.58		0.87	
		3 V	0.84		1.14	0.84		1.14	
		4.5 V	1.41		1.79	1.41		1.79	
		5.5 V	1.87		2.29	1.87		2.29	
ΔV_T Hysteresis $V_{T+} - V_{T-}$		1.65 V	0.37		0.62	0.37		0.62	V
		2.3 V	0.48		0.77	0.48		0.77	
		3 V	0.56		0.87	0.56		0.87	
		4.5 V	0.71		1.04	0.71		1.04	
		5.5 V	0.71		1.11	0.71		1.11	
V_{OH}	I_{OH} = –100 µA	1.65 V to 5.5 V	V_{CC} – 0.1			V_{CC} – 0.1			V
	I_{OH} = –4 mA	1.65 V	1.2			1.2			
	I_{OH} = –8 mA	2.3 V	1.9			1.9			
	I_{OH} = –16 mA	3 V	2.4			2.4			
	I_{OH} = –24 mA		2.3			2.3			
	I_{OH} = –32 mA	4.5 V	3.8			3.8			
V_{OL}	I_{OL} = 100 µA	1.65 V to 5.5 V			0.1			0.1	V
	I_{OL} = 4 mA	1.65 V			0.45			0.45	
	I_{OL} = 8 mA	2.3 V			0.3			0.3	
	I_{OL} = 16 mA	3 V			0.4			0.4	
	I_{OL} = 24 mA				0.55			0.75	
	I_{OL} = 32 mA	4.5 V			0.55			0.75	
I_I	V_I = 5.5 V or GND	0 to 5.5 V			±1			±5	µA
I_{off}	V_I or V_O = 5.5 V	0			±5			±10	µA
I_{CC}	V_I = 5.5 V or GND, I_O = 0	1.65 V to 5.5 V			10			10	µA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V			500			500	µA
C_I	V_I = V_{CC} or GND	3.3 V		4					pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	–40°C to 85°C								UNIT
				V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		
				MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A	Y	See Figure 3	4.3	9.2	2	6.2	1.2	5.4	1	4.1	ns
			See Figure 3	4.3	10.2	2	7.2	1.2	6.4	1	5.1	

6.7 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	f = 10 MHz	18	19	19	22	pF

6.8 Typical Characteristics

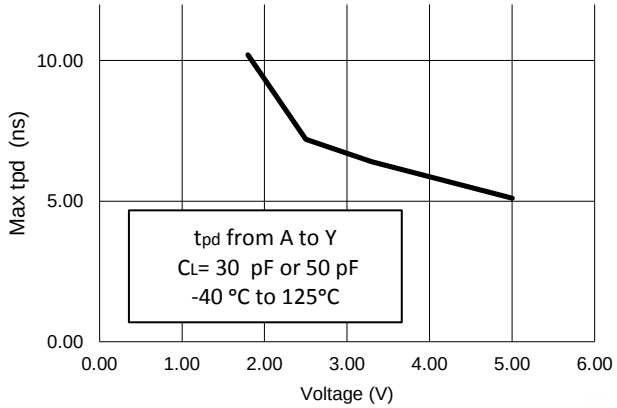
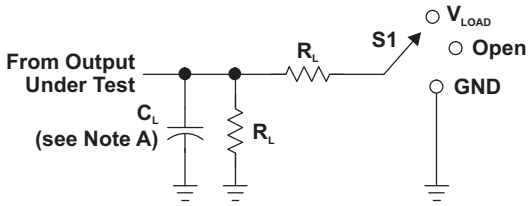


Figure 1. Maximum Propagation vs Delay V_{CC} Voltage

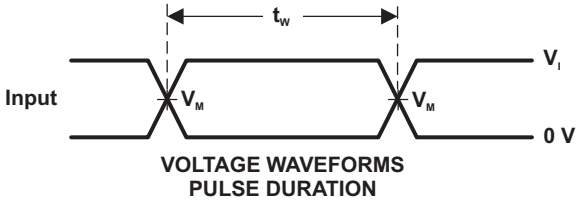
7 Parameter Measurement Information



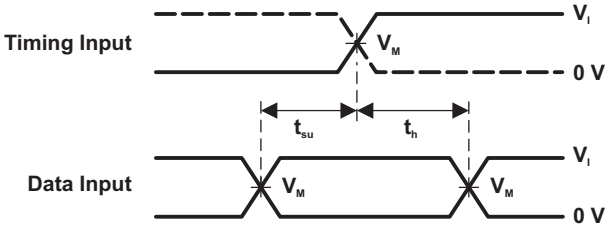
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

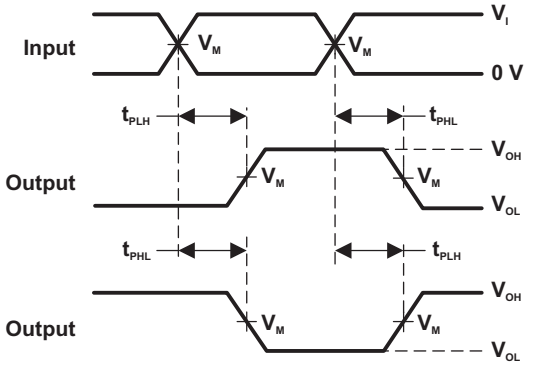
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 MΩ	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	15 pF	1 MΩ	0.3 V



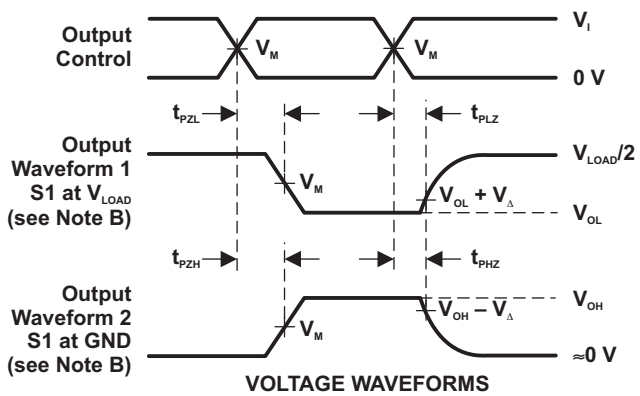
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS

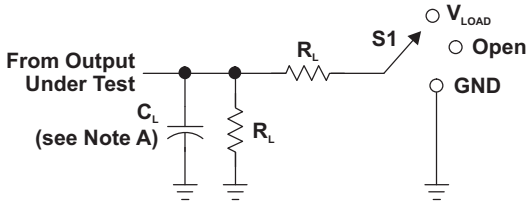


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 2. Load Circuit and Voltage Waveforms

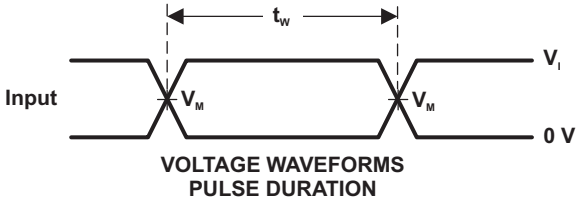
Parameter Measurement Information (continued)



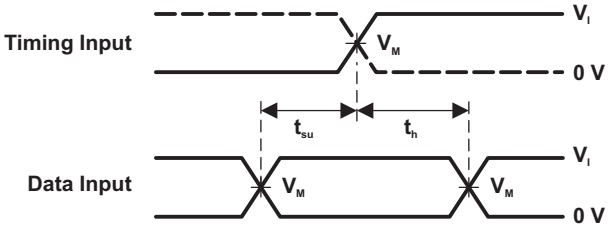
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

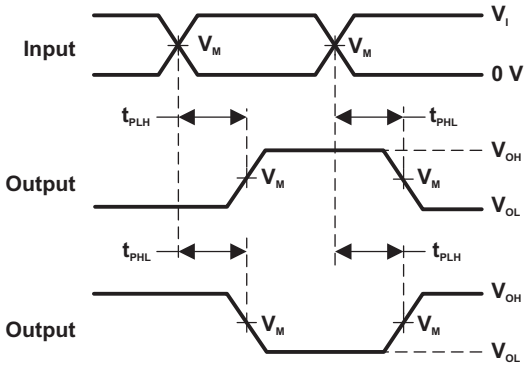
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	50 pF	500 Ω	0.3 V



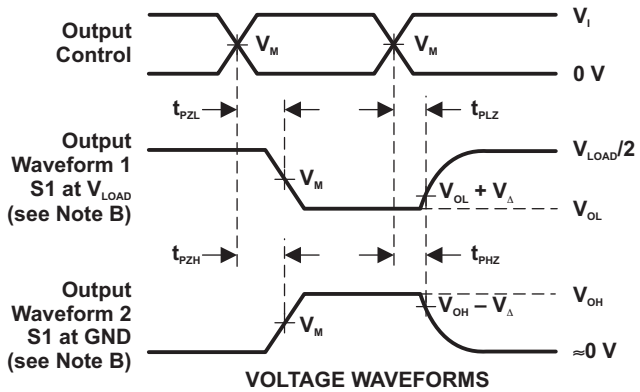
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
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H. All parameters and waveforms are not applicable to all devices.

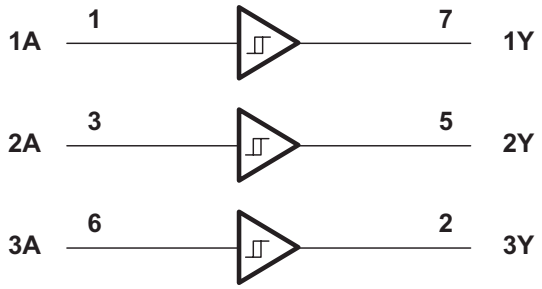
Figure 3. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

This triple Schmitt-trigger buffer is designed for 1.65-V to 5.5-V V_{CC} operation. The SN74LVC3G17 device contains three buffers and performs the Boolean function Y = A. The device functions as three independent buffers but, because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going ($V_{T–}$) signals. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

8.2 Functional Block Diagram



8.3 Feature Description

SN74LVC3G17 is available in NanoFree package. NanoFree is a major breakthrough in IC packaging concepts, it is a bare die package developed for applications that require the smallest possible package. The device supports 5-V V_{CC} Operation. All Inputs accept voltages up to 5.5 V. ±24-mA Output Drive at 3.3 V. The maximum time propagation delay (t_{pd}) is 5.4 ns at 3.3 V. Low Power Consumption, 10-µA Max I_{CC}. Typical output ground bounce (V_{OLP}) and Output V_{OH} Undershoot (V_{OHV}). This device is fully specified for partial-powerdown applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The SN74LVC3G17 device has isolation during power off. I_{off} supports live insertion, partial-power-down mode and back drive protection. The device is latch-up resistant with 100 mA exceeding the JESD 78 standard, class II, providing protection from destruction due to latch-up. This device is protected against electrostatic discharge. It is tested per JESD 22 using 2000-V human-body model (A114-B), 200-V machine model (A115-A), and 1000-V charged-device model (C101).

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC3G17.

Table 1. Function Table

INPUT A	OUTPUT Y
H	H
L	L

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC3G17 device contains three buffers and performs the Boolean function Y = A. The device functions as three independent buffers, but because of Schmitt action, it may have different input threshold levels for positive-going (V_{T+}) and negative-going (V_{T-}) signals. In this application, the engineer chooses to use just a single Schmitt Trigger buffer. In this case, the other two inputs should be tied to VCC or GND.

9.2 Typical Application

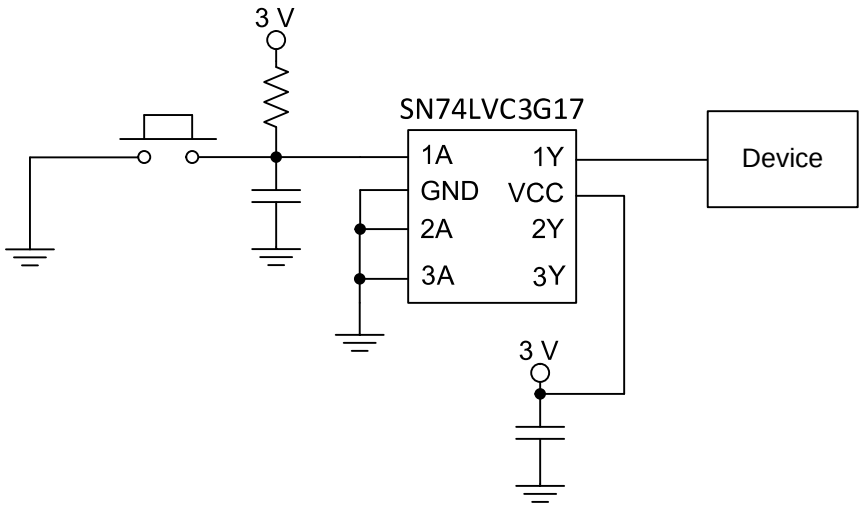


Figure 4. Device Power Button Circuit

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. Outputs can be combined to produce higher drive but the high drive will also create faster edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

1. Recommended Input Conditions:
   - For specified high and low levels, see (V_{IH} and V_{IL}) in *Recommended Operating Conditions* table.
   - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
2. Recommend Output Conditions:
   - Load currents should not exceed 50 mA per output and 100 mA total for the part.
   - Series resistors on the output may be used if the user desires to slow the output edge signal or limit the output current.

Typical Application (continued)

9.2.3 Application Curves

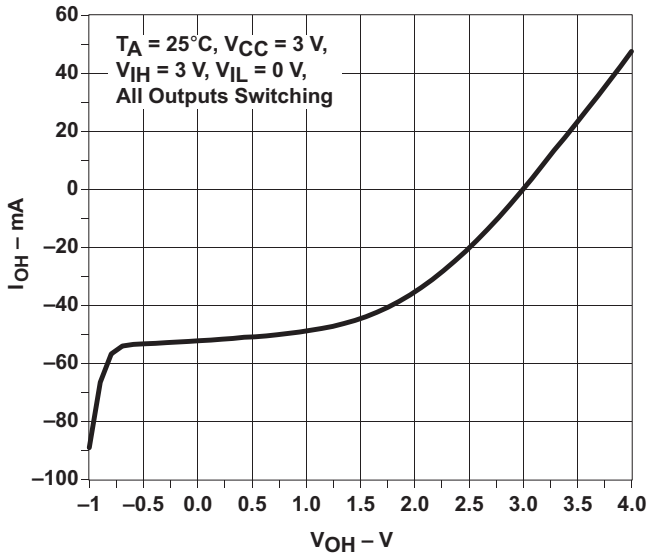


Figure 5. Output Current Drive vs HIGH-level Output Voltage

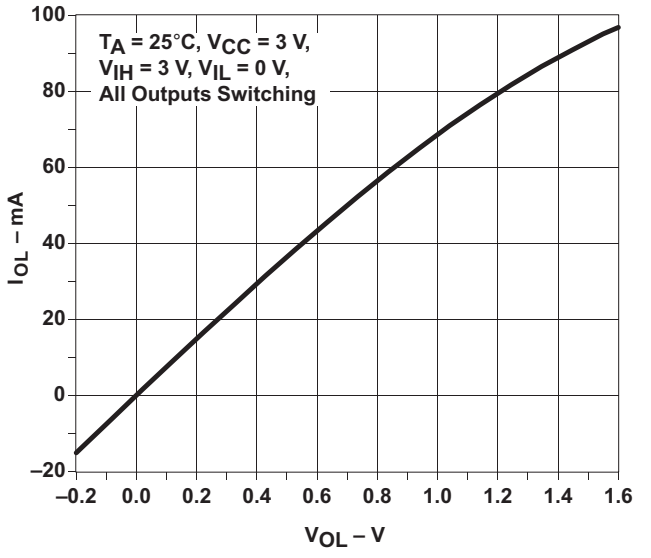


Figure 6. Output Current Drive vs LOW-level Output Voltage

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Absolute Maximum Ratings* table.

Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1-µF capacitor is recommended. If there are multiple V_{CC} terminals then 0.01-µF or 0.022-µF capacitors are recommended for each power terminal. It is ok to parallel multiple bypass capacitors to reject different frequencies of noise. Multiple bypass capacitors may be paralleled to reject different frequencies of noise. The bypass capacitor should be installed as close to the power terminal as possible for the best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 7 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient.

11.2 Layout Example

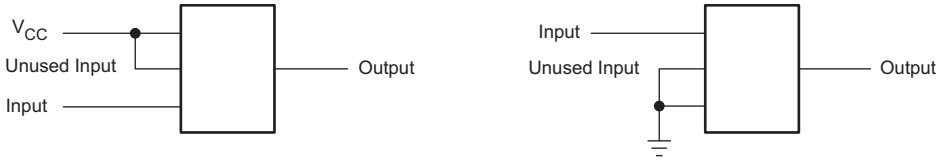


Figure 7. Layout Diagram

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

Implications of Slow or Floating CMOS Inputs, SCBA004

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

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12.4 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC3G17DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C17 Z	Samples
SN74LVC3G17DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C17 Z	Samples
SN74LVC3G17DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C17 Z	Samples
SN74LVC3G17DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-40 to 125	(17 ~ C17Q ~ C17R) CZ	Samples
SN74LVC3G17DCURE4	ACTIVE	VSSOP	DCU	8		TBD	Call TI	Call TI	-40 to 125		Samples
SN74LVC3G17DCURG4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	C17R	Samples
SN74LVC3G17YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(C77 ~ C7N)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

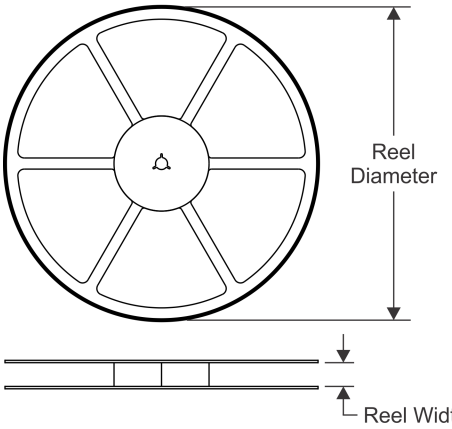
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

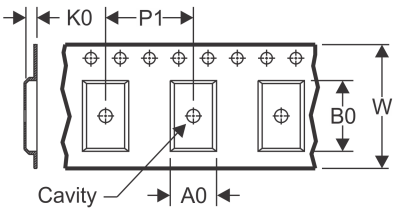
(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

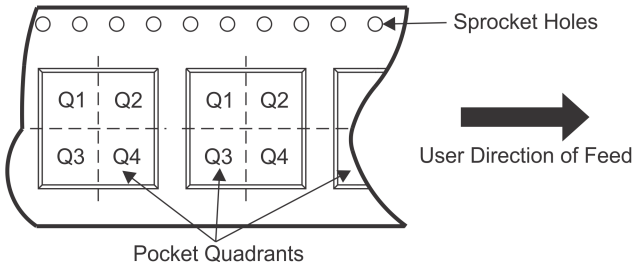


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

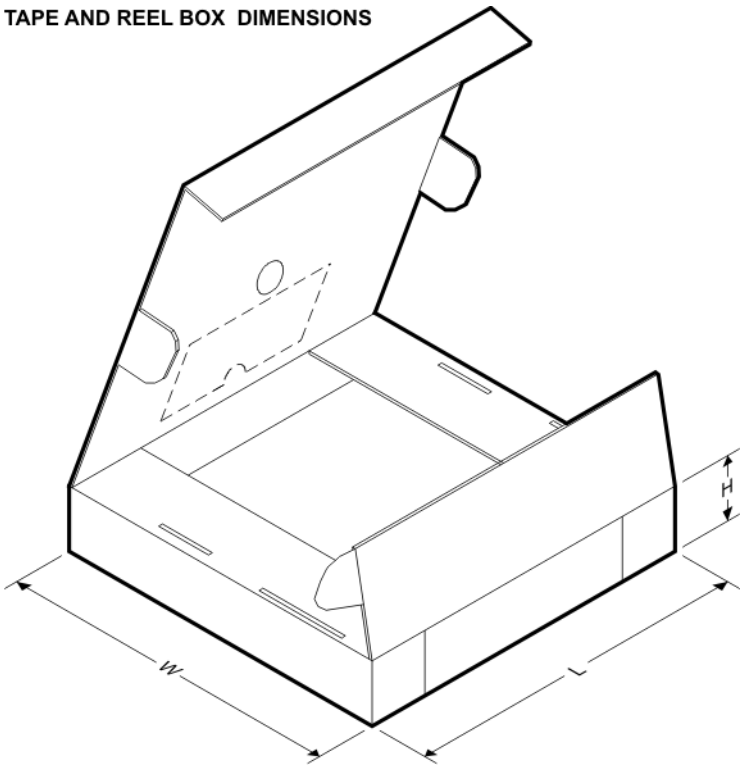
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC3G17DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC3G17DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC3G17DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.05	3.3	1.0	4.0	8.0	Q3
SN74LVC3G17DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC3G17YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS

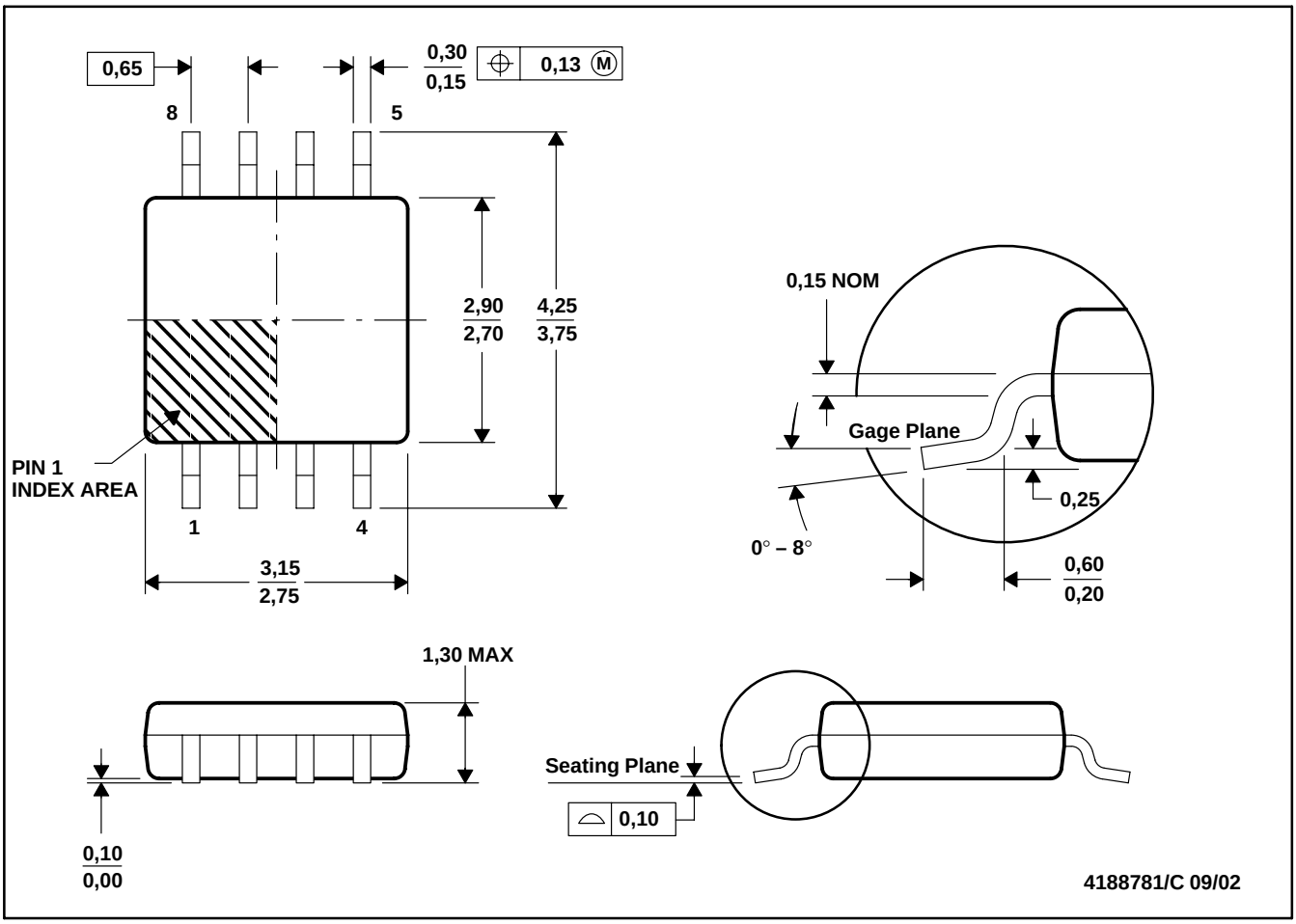


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC3G17DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC3G17DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC3G17DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74LVC3G17DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC3G17YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0

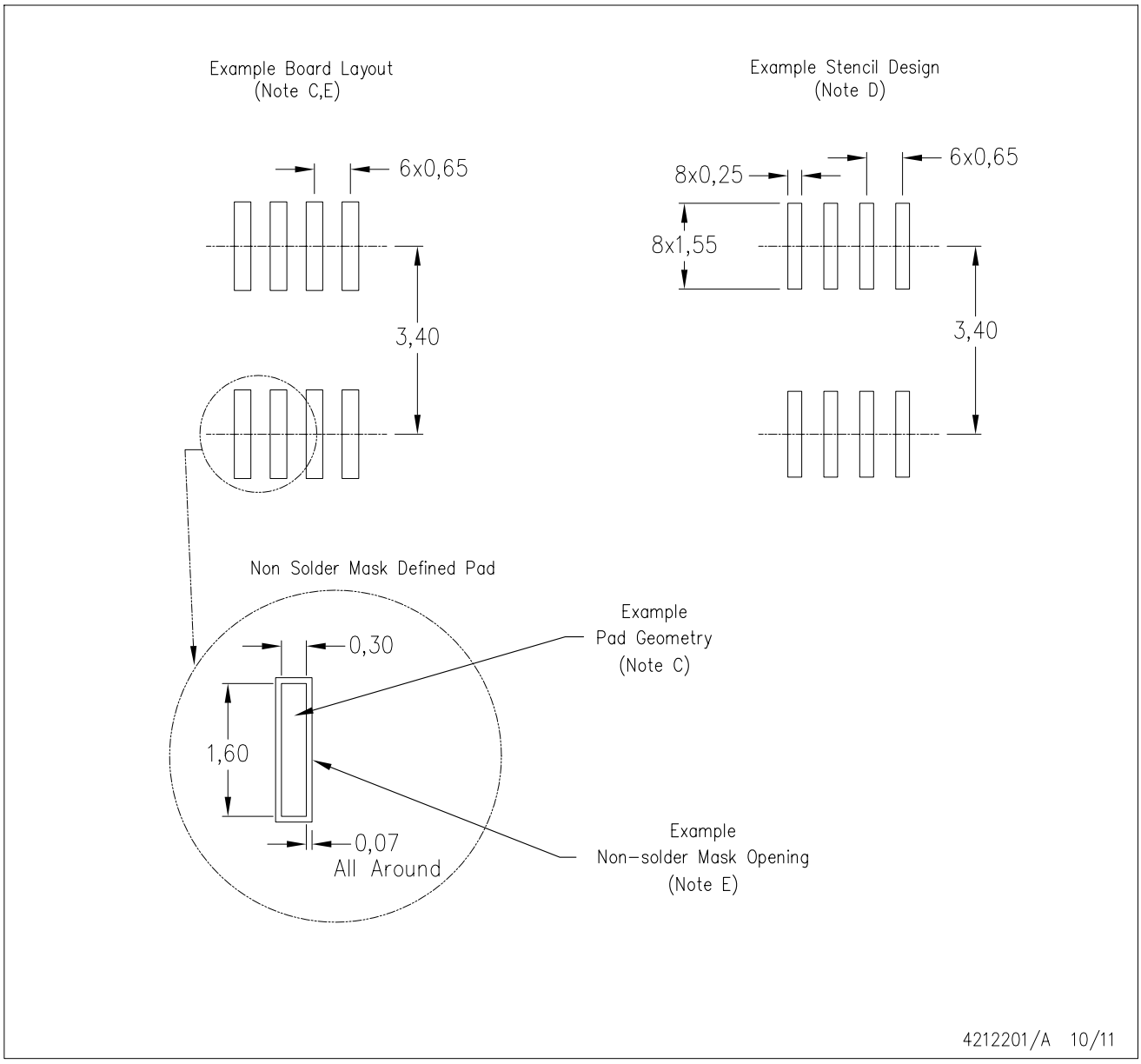
MPDS049B – MAY 1999 – REVISED OCTOBER 2002

DCT (R-PDSO-G8) **PLASTIC SMALL-OUTLINE PACKAGE**



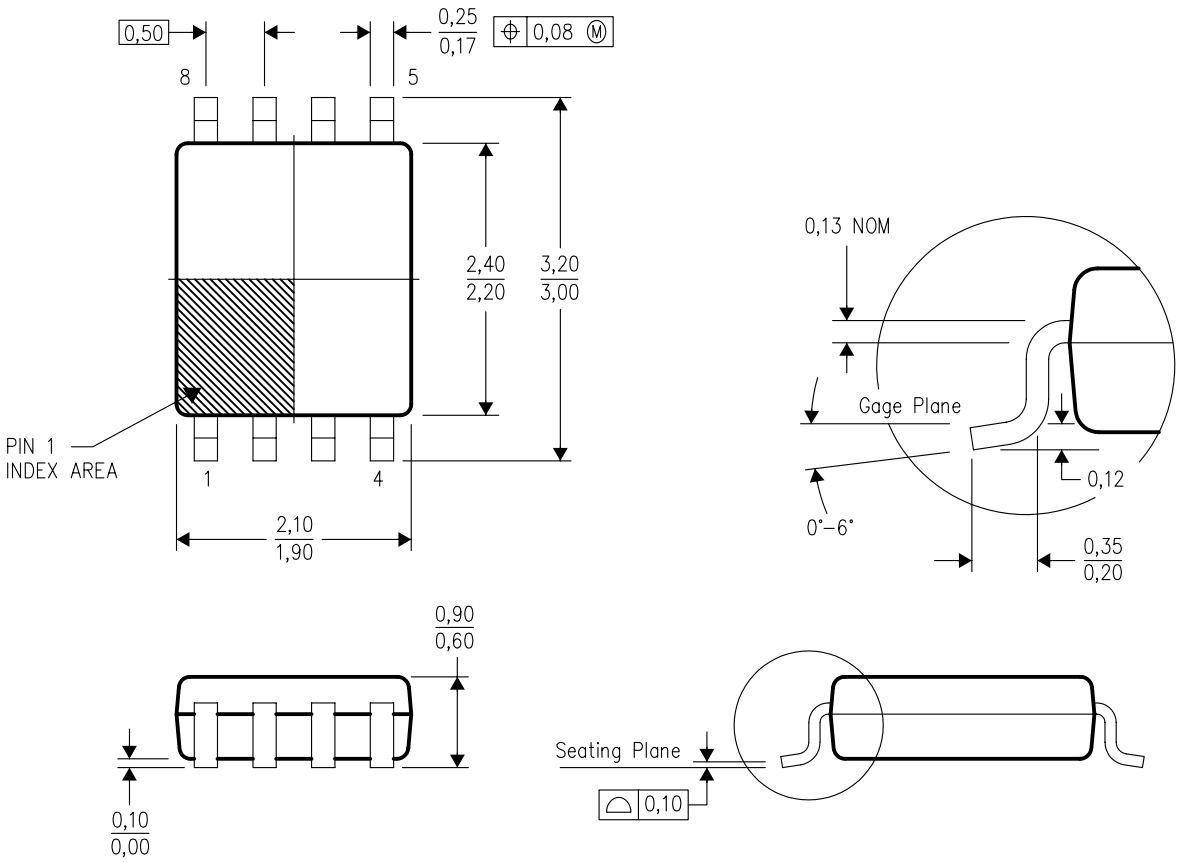
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion
D. Falls within JEDEC MO-187 variation DA.

DCT (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

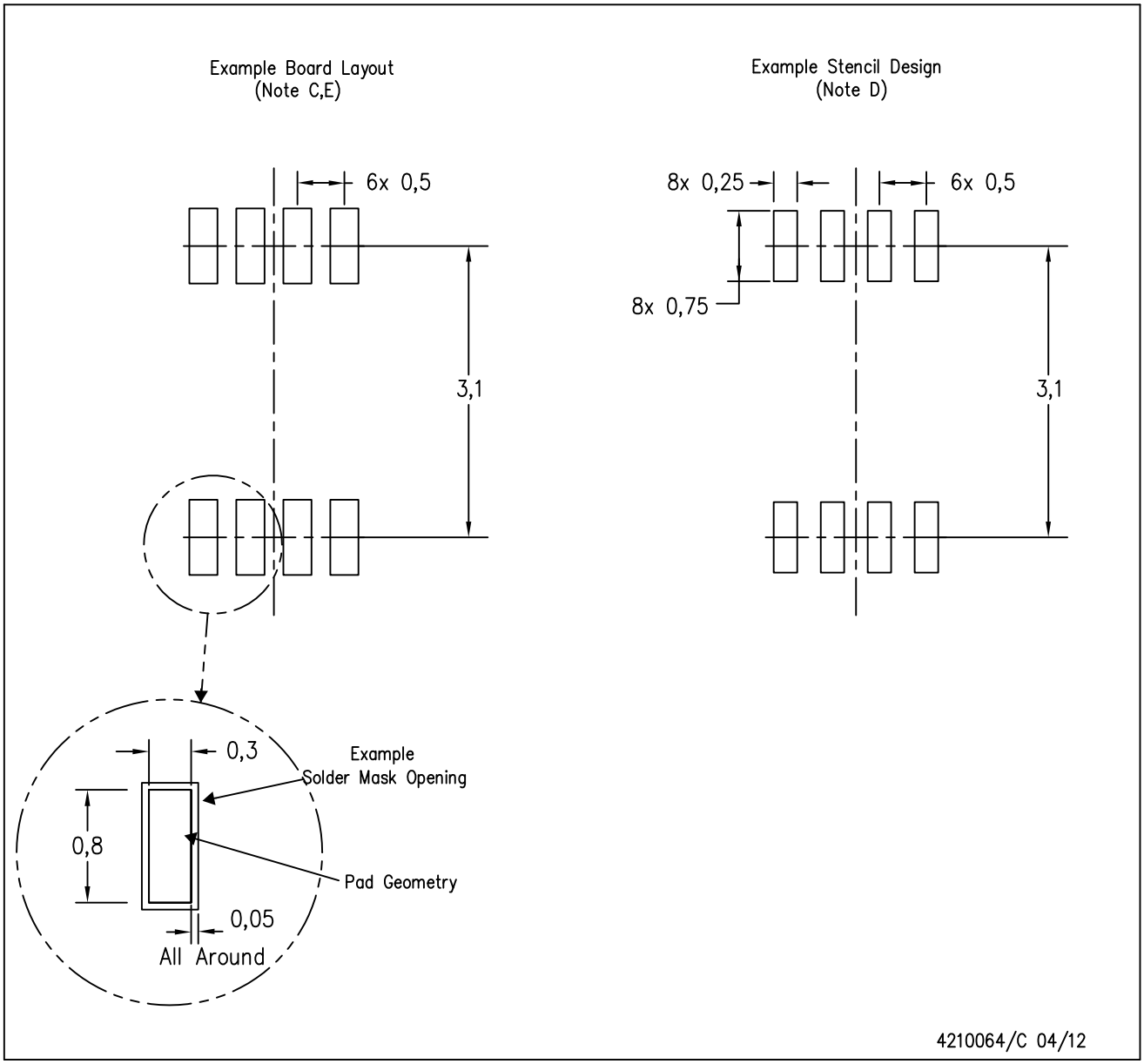
DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



4200503/F 07/05

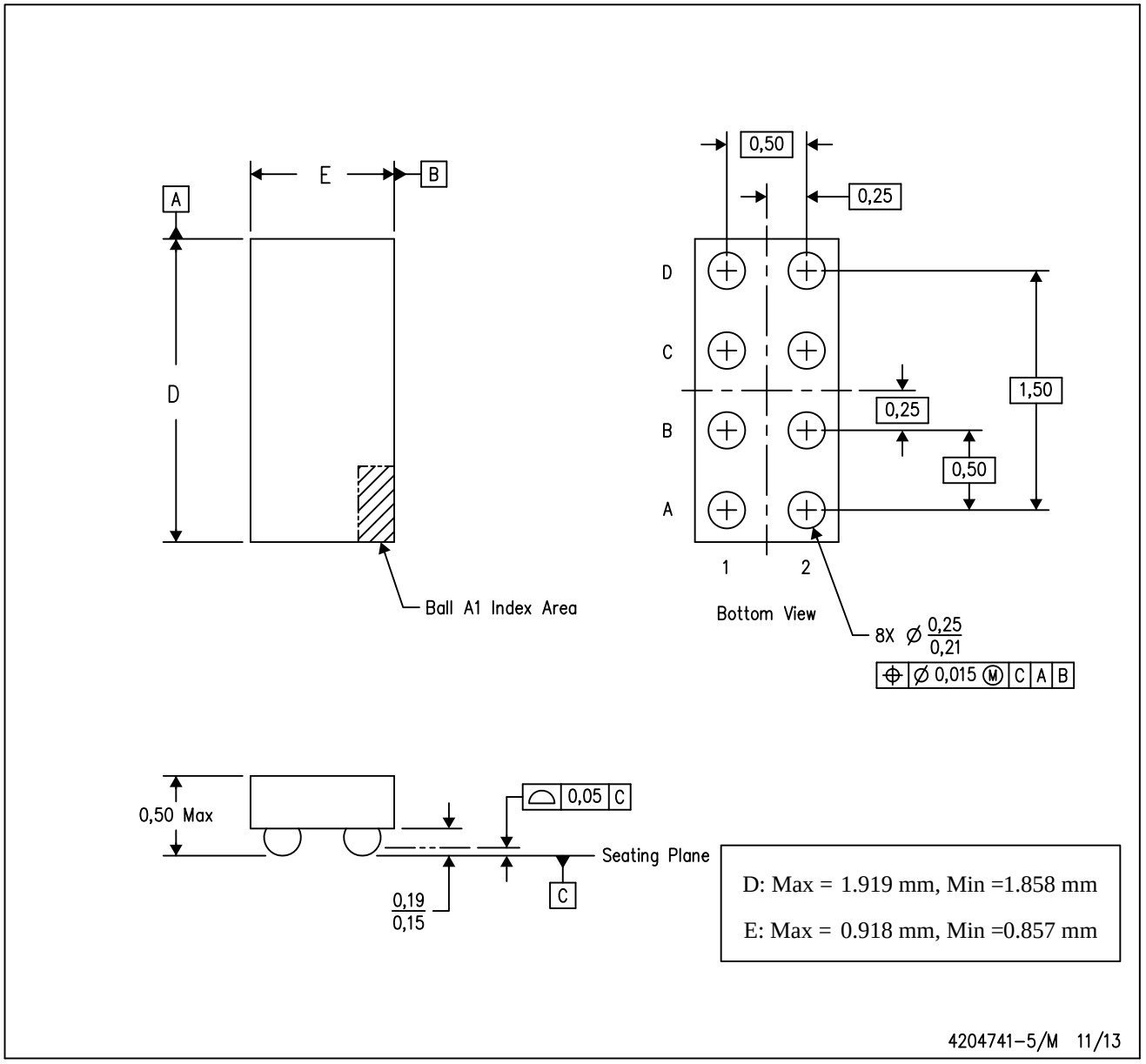
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

YZP (R–XBGA–N8) DIE–SIZE BALL GRID ARRAY



NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. NanoFree™ package configuration.

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